

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	12	jp-2000174137-\$.did. jp-2001274239-\$.did. jp-2000188331-\$.did. jp-10144673-\$.did. jp-2004031918-\$.did. jp-2003282703-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/02/03 13:08
L2	13	(transistor fet mos mosfet (field adj effect)) same (gate source drain) same (liner etchstop (etch adj stop) nitride) same ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) same (via opening hole contact) same (trace wir\$6 line interconnect\$6)	US-PGPUB; USPAT	OR	ON	2005/02/03 14:16
L3	12	(transistor fet mos mosfet (field adj effect) gate source drain) and (liner etchstop (etch adj stop) nitride) and ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and (via opening hole contact trace wir\$6 line interconnect\$6)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 14:20
L4	187	(transistor fet mos mosfet (field adj effect) gate source drain) same (liner etchstop (etch adj stop) nitride) same ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) same (via opening hole contact trace wir\$6 line interconnect\$6)	US-PGPUB; USPAT	OR	ON	2005/02/03 14:34
L5	104	(liner etchstop (etch adj stop) nitride) and ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and (via opening hole contact trace wir\$6 line interconnect\$6)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 14:51

L6	325	(438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and ((liner etchstop (etch adj stop) nitride) same ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) same (via opening hole contact trace wir\$6 line interconnect\$6))	US-PGPUB; USPAT	OR	ON	2005/02/03 14:59
L7	45	((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and ((438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and (hmds hexamethyldisilazane (silane adj coupler) (metal adj coupler)))	US-PGPUB; USPAT	OR	ON	2005/02/03 15:15
L8	18	((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and (borderless near contact)	US-PGPUB; USPAT	OR	ON	2005/02/03 15:23
L9	11	(borderless near contact) same ("low-k" "low k" (low adj (permittivity dielectric)))	US-PGPUB; USPAT	OR	ON	2005/02/03 15:25
L10	55	(borderless near contact) and (interlayer ild imd organic porous)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 15:27
L11	77	(438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and (borderless near contact)	US-PGPUB; USPAT	OR	ON	2005/02/03 15:29
L12	86	(porous near (silica (silicon adj (oxide dioxide)))) and ("low-k" "low k" (low adj (permittivity dielectric)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 15:32

L13	115	(438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and ((porous near (silica (silicon adj (oxide dioxide)))) same ("low-k" "low k" (low adj (permittivity dielectric))))	US-PGPUB; USPAT	OR	ON	2005/02/03 15:37
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